

	Type	Hits	Search Text	DBs	Time Stamp
1	IS&R	2	((("5374578") or ("5624864")).PN.	USPAT; US-PGPUB	2003/07/11 10:33
2	IS&R	1463	(438/3,240).CCLS.	USPAT; US-PGPUB	2003/07/11 10:33
3	BRS	258	((438/3,240).CCLS.) and @pd>20021206	USPAT; US-PGPUB	2003/07/11 10:34
4	IS&R	1	("6249014").PN.	USPAT; US-PGPUB	2003/07/11 10:50

	Document ID	Pages	Title	Current OR	Current XRef	Inventor
1	US 20030006439 A1	25	Hydrogen barrier encapsulation techniques for the control of hydrogen induced degradation of ferroelectric capacitors in conjunction with multilevel metal processing for non-volatile integrated circuit memory devices	257/295	438/3	Bailey, Richard A.
2	US 6249014 B1	24	Hydrogen barrier encapsulation techniques for the control of hydrogen induced degradation of ferroelectric capacitors in conjunction with multilevel metal processing for non-volatile integrated circuit memory devices	257/295	257/296; 257/306; 257/310; 257/E21.009; 257/E21.664; 257/E23.002	Bailey, Richard A.